

BC856BDW1T1, BC857BDW1T1 Series, BC858BDW1T1 Series

Preferred Devices

Dual General Purpose Transistors

PNP Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

- Device Marking:

BC856BDW1T1 = 3B

BC857BDW1T1 = 3F

BC857CDW1T1 = 3G

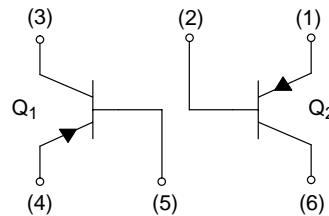
BC858BDW1T1 = 3K

BC858CDW1T1 = 3L

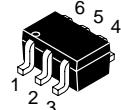


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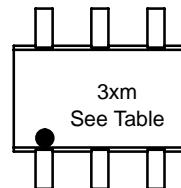
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DEVICE MARKING



SOT-363/SC-88
CASE 419B
Style 1



MAXIMUM RATINGS

Rating	Symbol	BC856	BC857	BC858	Unit
Collector-Emitter Voltage	V_{CEO}	-65	-45	-30	V
Collector-Base Voltage	V_{CBO}	-80	-50	-30	V
Emitter-Base Voltage	V_{EBO}	-5.0	-5.0	-5.0	V
Collector Current - Continuous	I_C	-100	-100	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	380 250 3.0	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = 1.0 x 0.75 x 0.062 in

3x = Specific Device Code

x = B, F, G, K, L

M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
BC856BDW1T1	SOT-363	3000 Units/Reel
BC857BDW1T1	SOT-363	3000 Units/Reel
BC857CDW1T1	SOT-363	3000 Units/Reel
BC858BDW1T1	SOT-363	3000 Units/Reel
BC858CDW1T1	SOT-363	3000 Units/Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = -10 \text{ mA}$)	$V_{(\text{BR})\text{CEO}}$	-65 -45 -30	-	-	V
Collector–Emitter Breakdown Voltage ($I_C = -10 \mu\text{A}$, $V_{\text{EB}} = 0$)	$V_{(\text{BR})\text{CES}}$	-80 -50 -30	-	-	V
Collector–Base Breakdown Voltage ($I_C = -10 \mu\text{A}$)	$V_{(\text{BR})\text{CBO}}$	-80 -50 -30	-	-	V
Emitter–Base Breakdown Voltage ($I_E = -1.0 \mu\text{A}$)	$V_{(\text{BR})\text{EBO}}$	-5.0 -5.0 -5.0	-	-	V
Collector Cutoff Current ($V_{\text{CB}} = -30 \text{ V}$) ($V_{\text{CB}} = -30 \text{ V}$, $T_A = 150^\circ\text{C}$)	I_{CBO}	-	-	-15 -4.0	nA μA
ON CHARACTERISTICS					
DC Current Gain ($I_C = -10 \mu\text{A}$, $V_{\text{CE}} = -5.0 \text{ V}$) ($I_C = -2.0 \text{ mA}$, $V_{\text{CE}} = -5.0 \text{ V}$)	h_{FE}	- - 220 420	150 270 290 520	- - 475 800	-
Collector–Emitter Saturation Voltage ($I_C = -10 \text{ mA}$, $I_B = -0.5 \text{ mA}$) ($I_C = -100 \text{ mA}$, $I_B = -5.0 \text{ mA}$)	$V_{\text{CE}(\text{sat})}$	- -	- -	-0.3 -0.65	V
Base–Emitter Saturation Voltage ($I_C = -10 \text{ mA}$, $I_B = -0.5 \text{ mA}$) ($I_C = -100 \text{ mA}$, $I_B = -5.0 \text{ mA}$)	$V_{\text{BE}(\text{sat})}$	- -	-0.7 -0.9	- -	V
Base–Emitter On Voltage ($I_C = -2.0 \text{ mA}$, $V_{\text{CE}} = -5.0 \text{ V}$) ($I_C = -10 \text{ mA}$, $V_{\text{CE}} = -5.0 \text{ V}$)	$V_{\text{BE}(\text{on})}$	-0.6 -	- -	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Current–Gain – Bandwidth Product ($I_C = -10 \text{ mA}$, $V_{\text{CE}} = -5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	100	-	-	MHz
Output Capacitance ($V_{\text{CB}} = -10 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_{ob}	-	-	4.5	pF
Noise Figure ($I_C = -0.2 \text{ mA}$, $V_{\text{CE}} = -5.0 \text{ Vdc}$, $R_S = 2.0 \text{ k}\Omega$, $f = 1.0 \text{ kHz}$, $BW = 200 \text{ Hz}$)	NF	-	-	10	dB

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TYPICAL CHARACTERISTICS – BC856

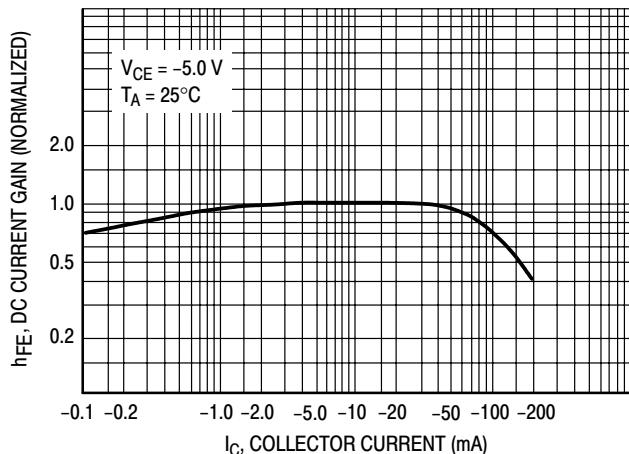


Figure 1. DC Current Gain

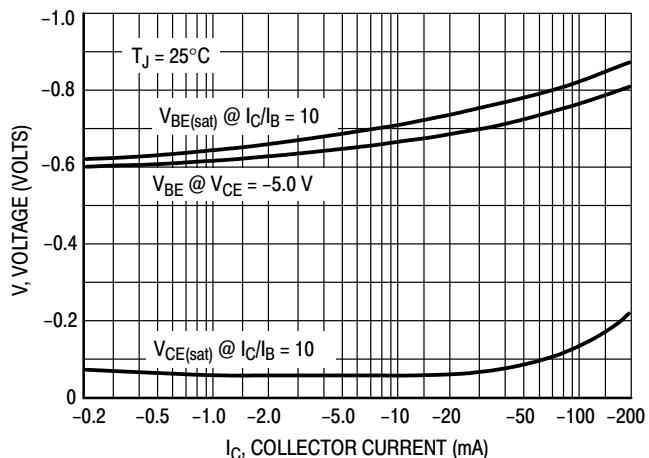


Figure 2. "On" Voltage

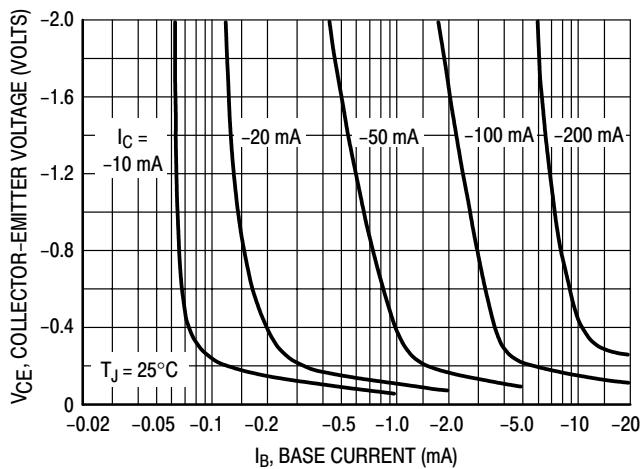


Figure 3. Collector Saturation Region

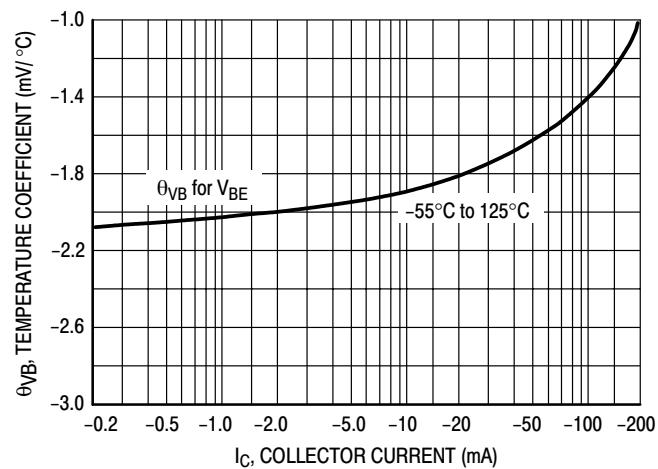


Figure 4. Base-Emitter Temperature Coefficient

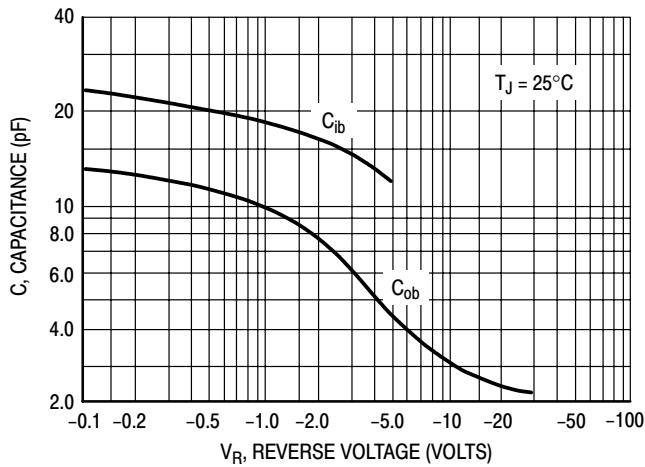


Figure 5. Capacitance

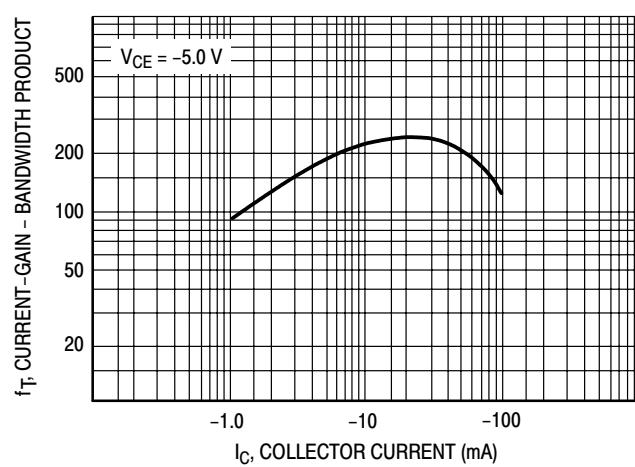


Figure 6. Current-Gain – Bandwidth Product

BC856BDW1T1, BC857BDW1T1 Series, BC858BDW1T1 Series

TYPICAL CHARACTERISTICS – BC857/BC858

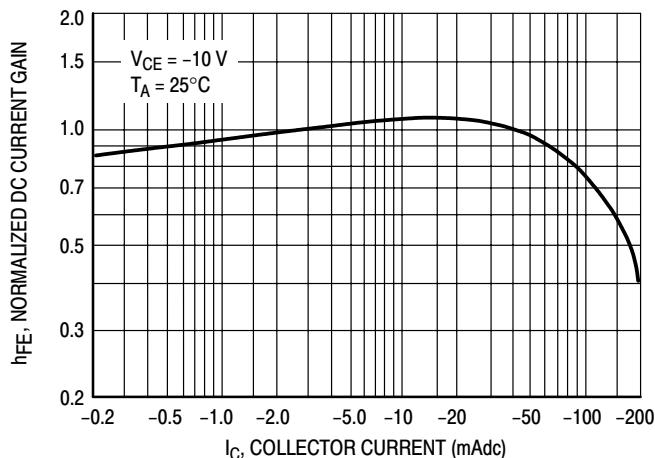


Figure 7. Normalized DC Current Gain

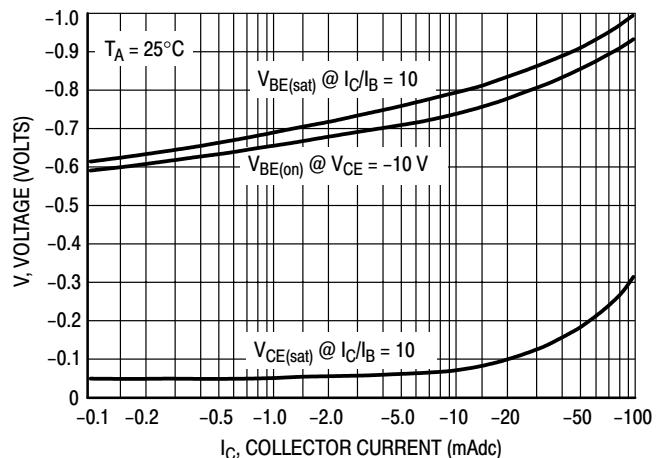


Figure 8. "Saturation" and "On" Voltages

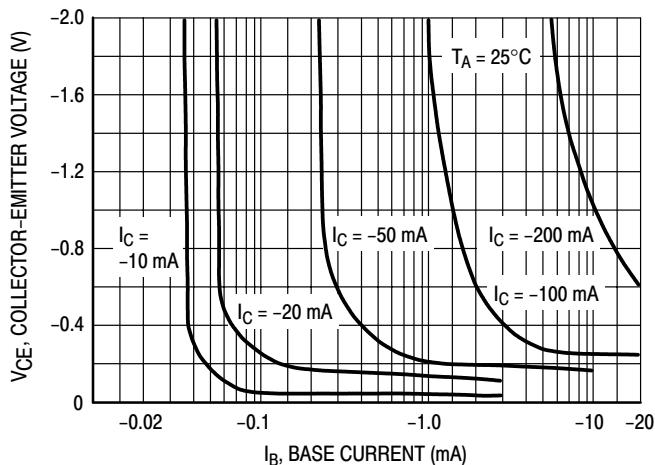


Figure 9. Collector Saturation Region

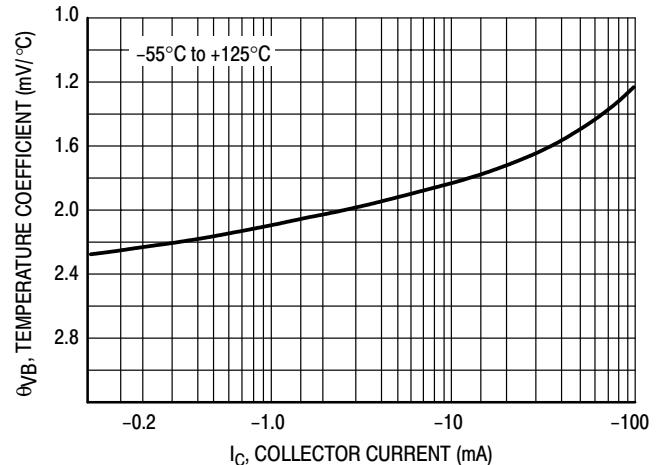


Figure 10. Base-Emitter Temperature Coefficient

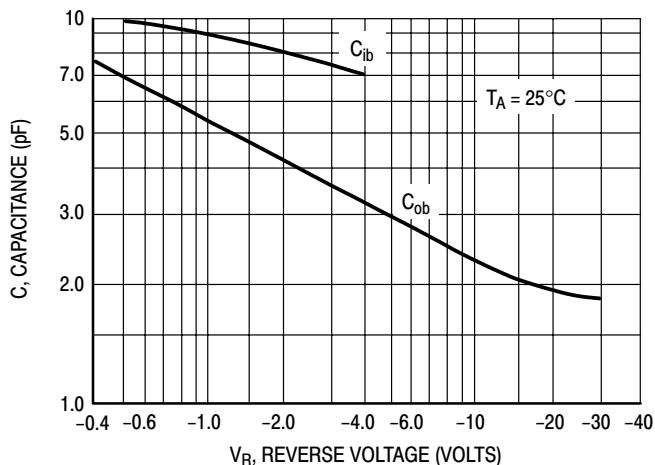


Figure 11. Capacitances

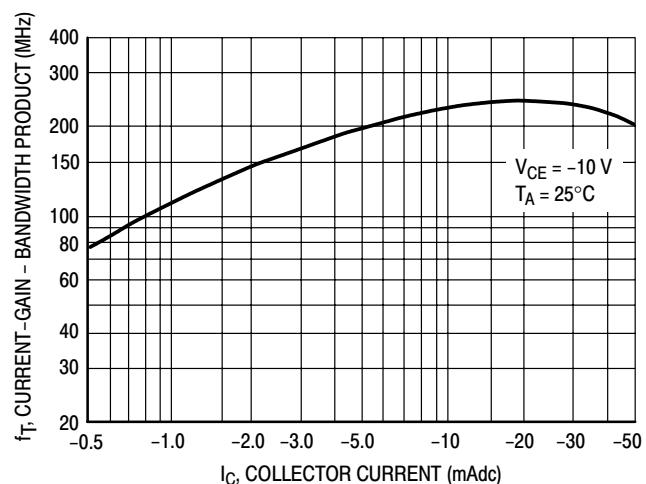


Figure 12. Current-Gain – Bandwidth Product

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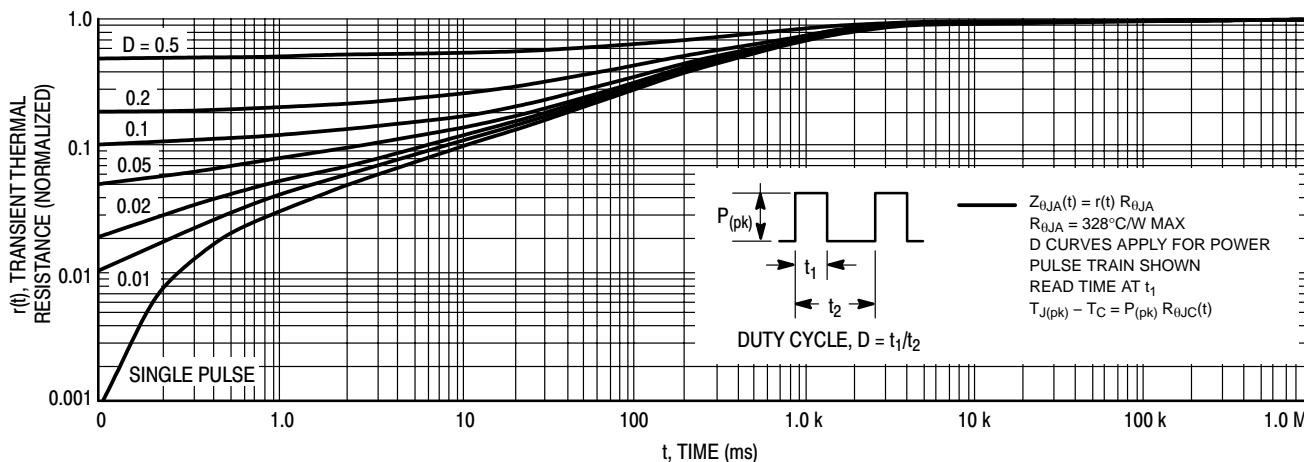


Figure 13. Thermal Response

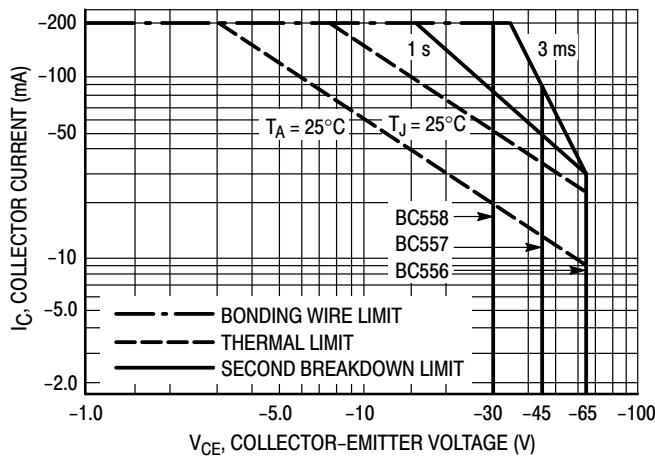


Figure 14. Active Region Safe Operating Area

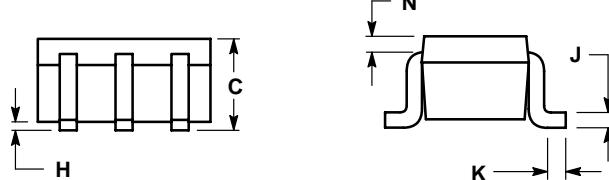
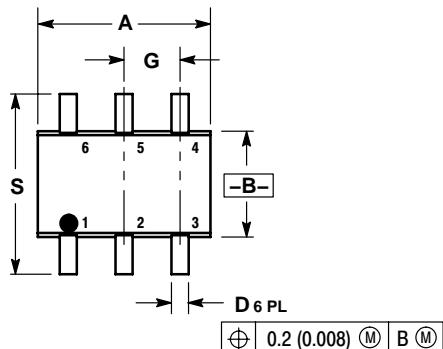
The safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150^\circ\text{C}$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

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PACKAGE DIMENSIONS

SC-88 (SOT-363) CASE 419B-02 ISSUE T

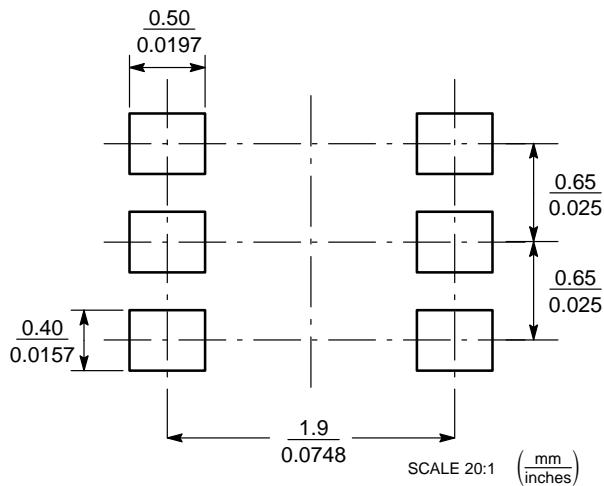


NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65	BSC
H	—	0.004	—	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008	REF	0.20	REF
S	0.079	0.087	2.00	2.20

STYLE 1:
 1. PIN 1. Emitter 2
 2. BASE 2
 3. COLLECTOR 1
 4. Emitter 1
 5. BASE 1
 6. COLLECTOR 2

SOLDERING FOOTPRINT*



SC-88/SC70-6

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